

# SOT-23-3L DIGITAL TRANSISTORS TRANSISTORS(PNP)

## **FEATURES**

- \* Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors.(see equivalent circuit).
- \* The bias resistors conisit of thin-film resistors with complete isolation to without connecting external input. They also have the advantage of almost completely Eliminating parasitic effects.
- \* Only the on/off conditions need to be set for operation marking device design easy.

### **MECHANICAL DATA**

- \* Case: Molded plastic
- \* Epoxy: UL 94V-O rate flame retardant
- \* Lead: MIL-STD-202E method 208C guaranteed
- \* Mounting position: Any \* Weight: 0.009 gram

# MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.



- (1) BASE (2) EMITTER
- (3) COLLECTOR

#### MAXIMUM RATINGES ( @ TA = 25°C unless otherwise noted )

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RATINGS	SYMBOL	VALUE	UNITS
Collector-Base Voltage	V <sub>CBO</sub>	-50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-50	V
Emitter-base Voltage	V <sub>EBO</sub>	-5	٧
Collector Continuous Current	Ic	-100	mA
Collector Dissipation	Pc	200	mW
Junction and storage Temperature	Тл ,Твтв	-55 to +150	°C

## **ELECTRICAL CHARACTERISTICS** ( @ TA = 25°C unless otherwise noted )

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNITS
Collector-base breakdown voltage (I <sub>C</sub> = -50μA,I <sub>E</sub> =0)	V <sub>(BR)CBO</sub>	-50	-	-	V
Collector-emitter breakdown voltage (I <sub>C</sub> = -1mA,I <sub>B</sub> =0)	V <sub>(BR)CEO</sub>	-50	-	-	V
Emitter-base breakdown voltage (I <sub>E</sub> = -50μA,I <sub>C</sub> =0)	V <sub>(BR)EBO</sub>	-5	-	-	V
Collector cut-off current (V <sub>CB</sub> = -50V,I <sub>E</sub> =0)	I <sub>CBO</sub>	-	-	-0.5	μА
Emitter cut-off current (V <sub>EB</sub> = -4V,I <sub>C</sub> =0)	I <sub>EBO</sub>	-	-	-0.5	μА
DC current gain (V <sub>CE</sub> = -5V,I <sub>C</sub> = -1mA)	h <sub>FE</sub>	100	250	600	
Collector-emitter saturation voltage (I <sub>C</sub> = -10mA,I <sub>B</sub> = -1mA)	V <sub>CE(sat)</sub>	-	-	-0.3	V
Transistion frequency (V <sub>CE</sub> = -10V,I <sub>C</sub> = -5mA,f=100MHz)	f <sub>T</sub>	-	250	-	MHz
Input resistor	R <sub>1</sub>	7	10	13	ΚΩ

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# RATING AND CHARACTERISTICS CURVES (DTA114TKA)

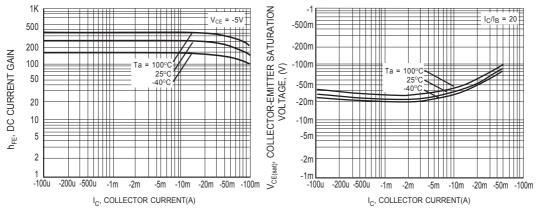


Figure 1 DC current gain vs. collector current

Figure 2 Collector-emitter saturation voltage vs.collector current

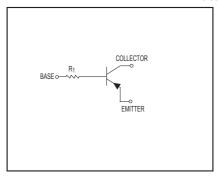


Figure3 Equivalent circuit

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